GN8062

GaAs IC

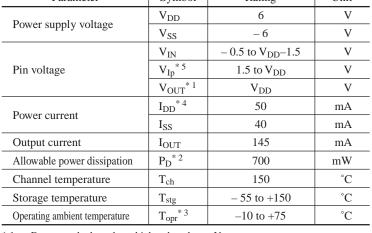
For semiconductor laser drive

■ Features

- High-speed switching
- High output
- Pulse current and DC bias current can be controlled.

■ Absolute Maximum Ratings (Ta = 25°C)

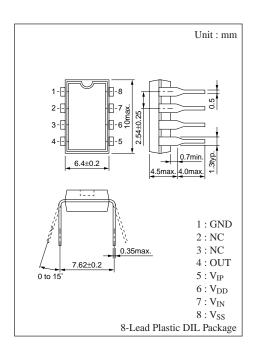
Parameter	Symbol	Rating	Unit	
D11	V_{DD}	6	V	
Power supply voltage	V _{SS}	-6	V	
	V _{IN}	- 0.5 to V _{DD} -1.5	V	
Pin voltage	V_{Ip}^{*5}	1.5 to V _{DD}	V	
	V _{OUT} * 1	V_{DD}	V	
Doving assument	I _{DD} * 4	50	mA	
Power current	I _{SS}	40	mA	
Output current	I _{OUT}	145	mA	
Allowable power dissipation	P _D * 2	700	mW	
Channel temperature	T _{ch}	150	°C	
Storage temperature	T _{stg}	- 55 to +150	°C	
Operating ambient temperature	Topr*3	-10 to +75	°C	



- Do not apply the voltage higher than the set V_{DD} .
- Guaranteed value of the unit at Ta= 25°C.
- Range in which the IC circuit function operates and not the guaranteed range of electric characteristics.
- I_{DD} is a current when the pulse output current is zero.
- Voltage when the constant current source has been connected.

■ Electrical Characteristics (Ta = 25°C)

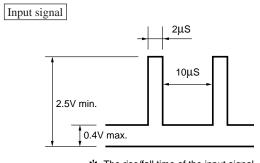
Parameter	Symbol	Test circuit	Condition	Min	Тур	Max	Unit
Pulse output current	I _{pmax} .	1	$V_{DD} = 5V$, $V_{SS} = -5V$, $V_{IN} = 2V$, $I_p = 120$ mA, $R_L = 10\Omega$	100	120		mA
	I _{pmin} .	1	V_{DD} = 5V, V_{SS} = -5V, V_{IN} = 0.4V, I_p =120mA, R_L =10 Ω		1	5	mA
Supply current $\frac{{\rm I_{DD}}^*}{{\rm I_{SS}}}$	I _{DD} * 1	2	$V_{DD} = 5V, V_{SS} = -5V, V_{IN} = 0.4V$		35	50	mA
	I _{SS}	2	$I_p = 0, R_L = 10\Omega$		25	40	mA
Input voltage V_{IH} V_{IL}	V _{IH}			2.5			V
	V _{IL}					0.4	V
Rise time	t _r * 2	3	$V_{DD} = 5V, V_{SS} = -5V, I_p = 100 \text{mA}$			7	ns
Fall time	t _f * 2	3	R_L =10 Ω			5	ns



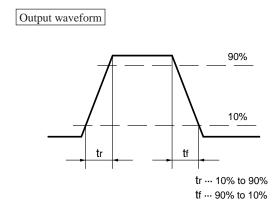
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*1 The current value to be supplied from the 5V power supply is a total sum of this value plus the pulse output current and bias output current.

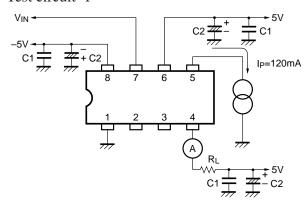
* 2 Waveform of input and output signals



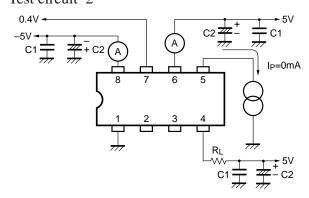
The rise/fall time of the input signal is 2ns (10 to 90%)



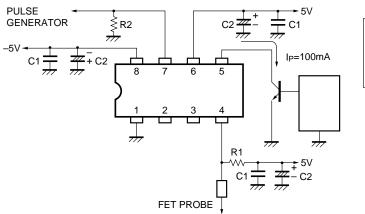




Test circuit 2

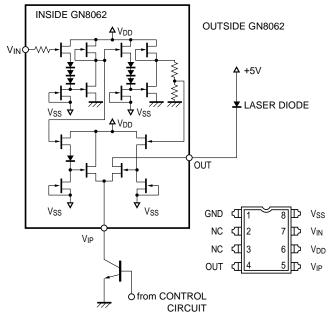


Test circuit 3



 $C_1: 0.1 \mu F$ $C_2: 3.3 \mu F$ $R_1: 10 \Omega$ $R_2: 50 \Omega$ GaAs MMICs GN8062

■ Block Diagram



■ Caution for Handling

- 1) The recommended V_{IN} voltage is 2.5 to 3V for [H] and 0 to 0.4V for [L].
- 2) Do not apply V_{IN} while the power supply is OFF.
- 3) For the current source to be connected to the V_{IP} pin, use a Si bipolar transistor as shown in the circuit diagram.

(Example: 2SD874)

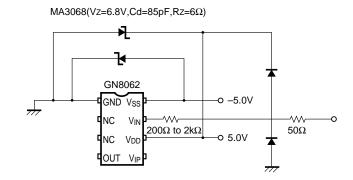
To connect a resistor to the emitter or collector, use a resistor of a few ohm. The use of higher resistor may cause large change in the voltage at the V_{IP} pin, and may make the output waveform distortion. (See the pulse output current control example).

To use another current control circuit, set so that the V_{IP} pin voltage becomes around 2V.

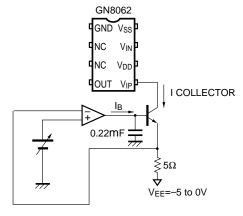
- 4) When mounting, minimize the connection distance between the semiconductor laser and IC, and use the chip parts (C, R) of less parasitic effects.
- 5) Attention to damage by the power surge (see the example connection of the pin protection circuit). During handling, take care to ground the human body and solder iron tip.
- 6) When the power supply is turned ON and OFF, set the current value of the current source connected to the V_{IP} pin to zero. This is important to prevent the large current flow through the semiconductor laser during power ON/OFF.

When the power supply is ON, be sure to turn ON $V_{\rm DD}$, after $V_{\rm SS}$ is completely equal to – 5V. When the power supply is OFF, be sure to turn OFF $V_{\rm SS}$, after $V_{\rm DD}$ is completely 0V.

7) Pay attention to release the heat.



Connection example of pin protection circuit



Example of pulse output current control circuit